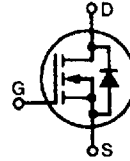


MegaMOS™ FET

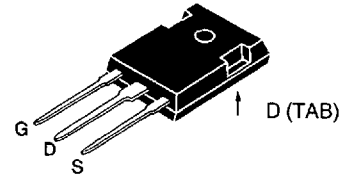
N-Channel Enhancement Mode

	V_{DSS}	I_{D25}	$R_{DS(on)}$
IXTH 30N45	450 V	30 A	0.16 Ω
IXTH 30N50	500 V	30 A	0.17 Ω

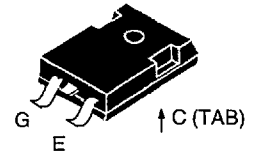


Symbol	Test Conditions	Maximum Ratings		
		30N45	30N50	Unit
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	450	500	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1\text{ M}\Omega$	450	500	V
V_{GS}	Continuous	± 20		V
V_{GSM}	Transient	± 30		V
I_{D25}	$T_C = 25^\circ\text{C}$	30		A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	120		A
P_D	$T_C = 25^\circ\text{C}$	360		W
T_J		-55 ... +150		$^\circ\text{C}$
T_{JM}		150		$^\circ\text{C}$
T_{stg}		-55 ... +150		$^\circ\text{C}$
T_L	1.6 mm (0.063 in) from case for 10 s	300		$^\circ\text{C}$
M_d	Mounting torque	1.13/10		Nm/lb.in.
Weight		6		g

TO-247 AD



TO-247 SMD (...S)



G = Gate, D = Drain,
S = Source, TAB = Drain

*Add suffix letter "S" for TO-247 SMD package option (EX: IXTH30N50S)

Features

- International standard package JEDEC TO-247 AD
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- High commutating dv/dt rating
- Fast switching times

Applications

- Switch-mode and resonant-mode power supplies
- Motor control
- Uninterruptible Power Supplies (UPS)
- DC choppers

Advantages

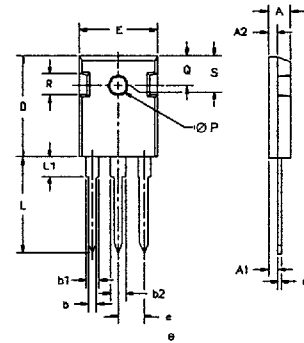
- Easy to mount with 1 screw (TO-247) (isolated mounting screw hole)
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0\text{ V}$, $I_D = 5\text{ mA}$	30N50 500	30N45 450	V
	BV_{DSS} temperature coefficient		.087	%/k
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	2		4 V
	$V_{GS(th)}$ temperature coefficient		-0.25	%/k
I_{GSS}	$V_{GS} = \pm 20\text{ V}_{DC}$, $V_{DS} = 0$			$\pm 100\text{ nA}$
I_{DSS}	$V_{DS} = 0.8 \cdot V_{DSS}$, $V_{GS} = 0\text{ V}$	$T_J = 25^\circ\text{C}$ 200	$T_J = 125^\circ\text{C}$ 3	μA mA
$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 0.5 I_{D25}$	30N50 0.17	30N45 0.16	Ω Ω
	Pulse test, $t \leq 300\mu\text{s}$, duty cycle $d \leq 2\%$			

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$, pulse test	18	28	S
C_{iss} C_{oss} C_{rss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		5680	pF
			635	pF
			240	pF
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 1\ \Omega$, (External)		35	ns
			42	ns
			110	ns
			26	ns
$Q_{g(on)}$ Q_{gs} Q_{gd}	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 I_{D25}$		227	nC
			29	nC
			110	nC
R_{thJC} R_{thCK}		0.15	0.35	K/W K/W

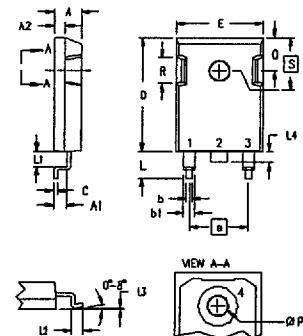
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
I_S	$V_{GS} = 0$			30 A
I_{SM}	Repetitive; pulse width limited by T_{JM}			120 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.5 V
t_{tr}	$I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$		850	ns

TO-247 AD Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

TO-247 SMD Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A1	2.29	2.54	.090	.100
A2	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b1	1.91	2.13	.075	.084
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45	BSC	.215	BSC
L	4.90	5.10	.193	.201
L1	2.70	2.90	.106	.114
L2	2.10	2.30	.083	.091
L3	0.00	0.10	.00	.004
L4	1.90	2.10	.075	.083
ØP	3.55	3.65	.140	.144
Q	5.59	6.20	.220	.244
R	4.32	4.83	.170	.190
S	6.15	BSC	.242	BSC

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025